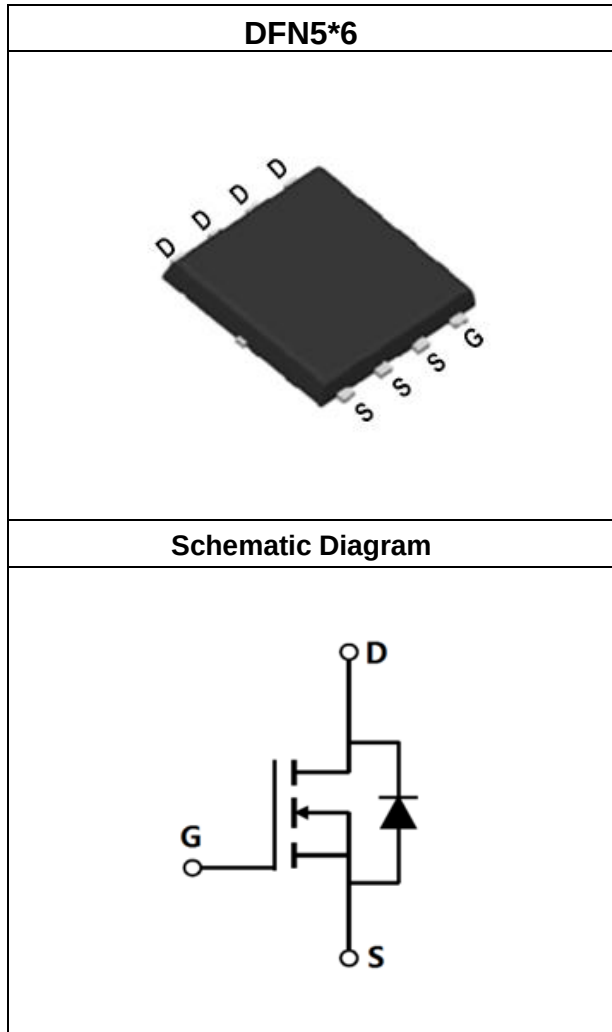


N-channel 60V, 7.5mΩ typ.,
SGT MOSFET S2 in DFN5*6

Datasheet - production data

1. Descriptions



Key Performance Parameters

Parameters	Value	Unit
BV_{DSS}	60	V
$R_{DS(on),max}$	9	mΩ
P_D	62.5	W
I_D	60	A

Features

- High Speed Power Switching, Logic level
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- 100% UIS Tested, 100% Rg Tested
- Lead Free, Halogen Free

Applications

- DC/DC Converter
- Motor Drivers
- Ideal for high-frequency switching and synchronous rectification

Type/Ordering Code	Package	Marking	Related Links
CSLS090N06S2	DFN5*6	090N06S2	see Appendix A

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2. Maximum Ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Absolute Maximum Ratings

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
V_{DS}	Drain-source voltage	-	-	60	V	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$
V_{GS}	Gate source voltage	-20	-	20	V	static; AC ($f>1\text{ Hz}$)
I_D	Continuous drain current	-	-	60 43	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
$I_{D,pulse}$	Pulsed drain current	-	-	240	A	$T_C=25^\circ\text{C}$
P_D	Power dissipation DFN5*6	-	-	62.5	W	$T_C=25^\circ\text{C}$
E_{AS}	Avalanche energy, single pulse ¹⁾	-	-	180	mJ	$I_D=6\text{A}$; $V_{DD}=50\text{V}$
T_j, T_{stg}	Operating and storage temperature	-55	-	150	$^\circ\text{C}$	-

3. Thermal Characteristics

Thermal Characteristics (DFN5*6)

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
R_{thJC}	Thermal resistance, junction - case	-	-	2	$^\circ\text{C/W}$	$T_C = 25^\circ\text{C}$
R_{thJA}	Thermal resistance, junction - ambient	-	-	75	$^\circ\text{C/W}$	$T_C = 25^\circ\text{C}$

4. Electrical Characteristics

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		

Off Characteristics

$V_{(BR)DSS}$	Drain-source breakdown voltage	60	-	-	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Zero gate voltage drain current	-	-	1	μA	$V_{DS}=60V, V_{GS}=0V$
I_{GSS}	Gate-source leakage current	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$

On Characteristics³⁾

$V_{(GS)th}$	Gate threshold voltage	1.0	1.8	2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$R_{DS(on)}$	Drain-source on-state resistance	-	7.5 10	9 14	m Ω	$V_{GS}=10V, I_D=20A$ $V_{GS}=4.5V, I_D=10A$
R_G	Gate resistance	-	2.6	-	Ω	$V_{DD}=0V, V_{GS}=0V, F=1MHz$
g_{fs}	Transconductance	-	80	-	S	$V_{DS}=5V, I_D=20A$

Dynamic Characteristics

C_{iss}	Input capacitance	-	1480	-	pF	$V_{GS}=0V, V_{DS}=30V,$ $F=1MHz$
C_{oss}	Output capacitance	-	290	-	pF	
C_{rss}	Reverse transfer capacitance	-	4.1	-	pF	

Switching Characteristics⁴⁾

$t_{d(on)}$	Turn-on delay time	-	11	-	ns	$V_{DD}=30V, V_{GS}=10V,$ $I_D=14.5A, R_G=3\Omega$
t_r	Turn-on rise time	-	5	-	ns	
$t_{d(off)}$	Turn-off delay time	-	56	-	ns	
t_f	Turn-off fall time	-	12	-	ns	
Q_g	Gate charge total	-	23	-	nC	$V_{DD}=30V, I_D=14.5A, V_{GS}=10V$
Q_{gs}	Gate to source charge	-	4.8	-	nC	
Q_{gd}	Gate to drain charge	-	2.4	-	nC	

Reverse Diode Characteristics

V_{SD}	Diode forward voltage ³⁾	-	0.9	1.2	V	$V_{GS}=0V, I_F=20A$
I_S	Diode forward current ²⁾	-	-	60	A	
t_{rr}	Reverse recovery time	-	32	-	ns	$V_{GS}=0V, I_F=14.5A,$ $di/dt=100A/\mu s^3)$
Q_{rr}	Reverse recovery charge	-	46	-	nC	

1) $V_{DD}=50V, L=10mH, R_G=25\Omega$, Starting $T_j=25^\circ\text{C}$.

2) Surface Mounted on FR4 Board, $t \leq 10$ sec.

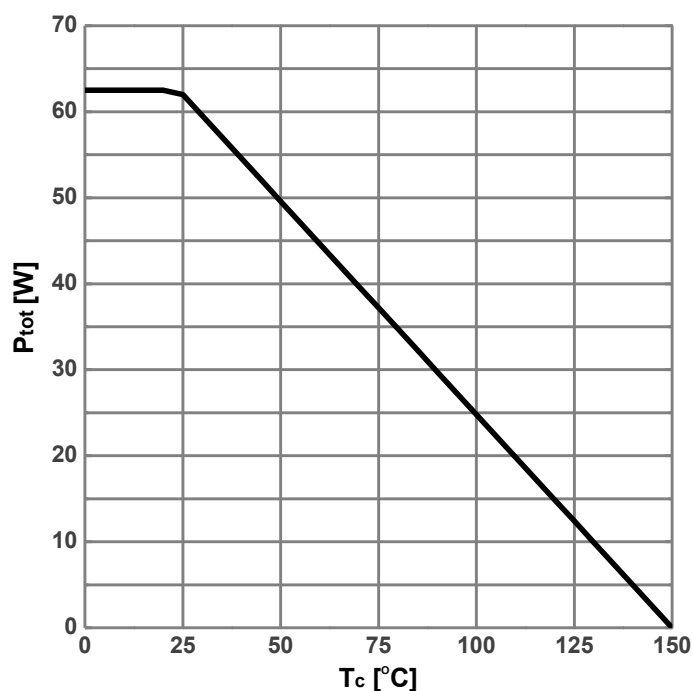
3) Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

4) Guaranteed by design, not subject to production

5) Repetitive Rating: Pulse width limited by maximum junction temperature.

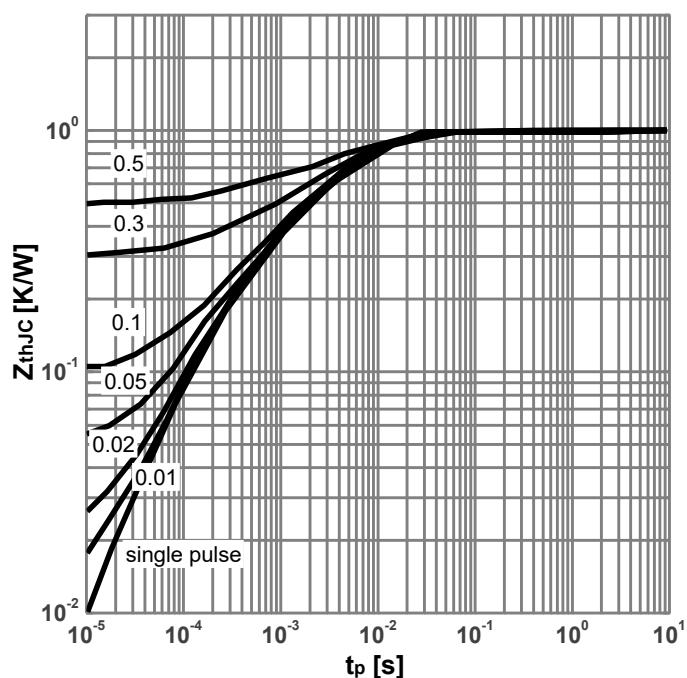
5. Electrical Characteristics Diagrams

Diagram 1: Power dissipation (DFN5*6)



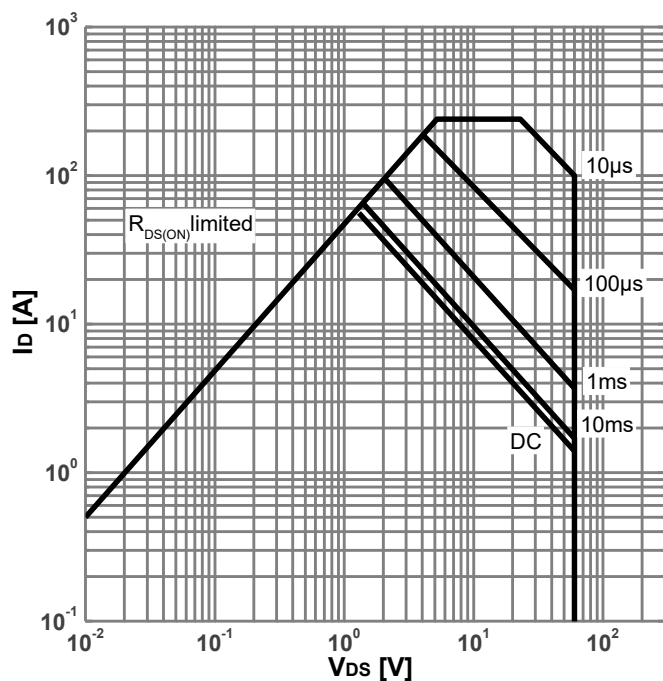
$$P_{\text{tot}} = f(T_c)$$

Diagram 2: Max. transient thermal impedance (DFN5*6)



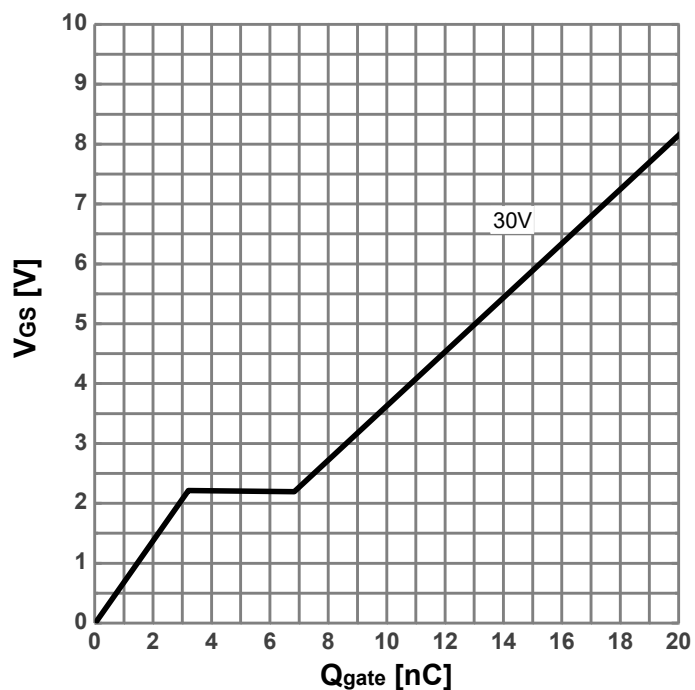
$$Z_{\text{thJC}} = f(t_p); \text{ parameter: } D = t_p/T$$

Diagram 3: Safe operating area (DFN5*6)



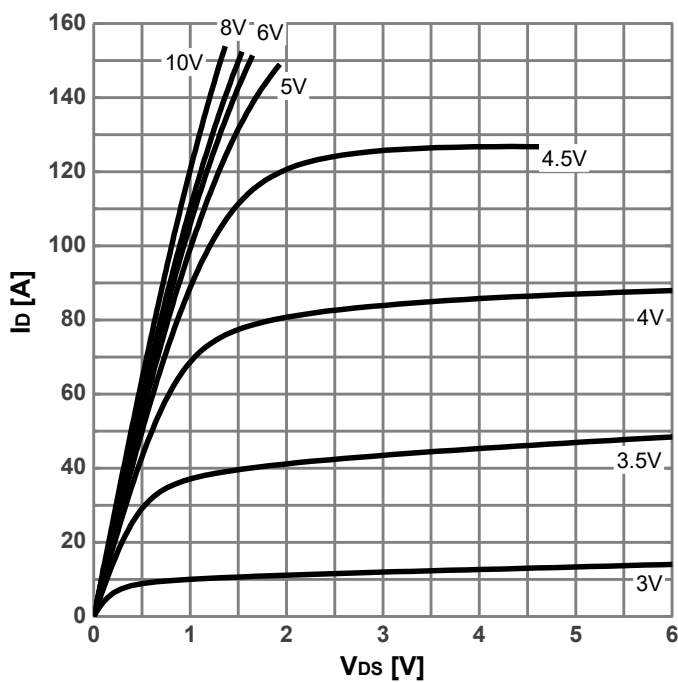
$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}; D = 0; \text{ parameter: } t_p$$

Diagram 4: Typ. gate charge



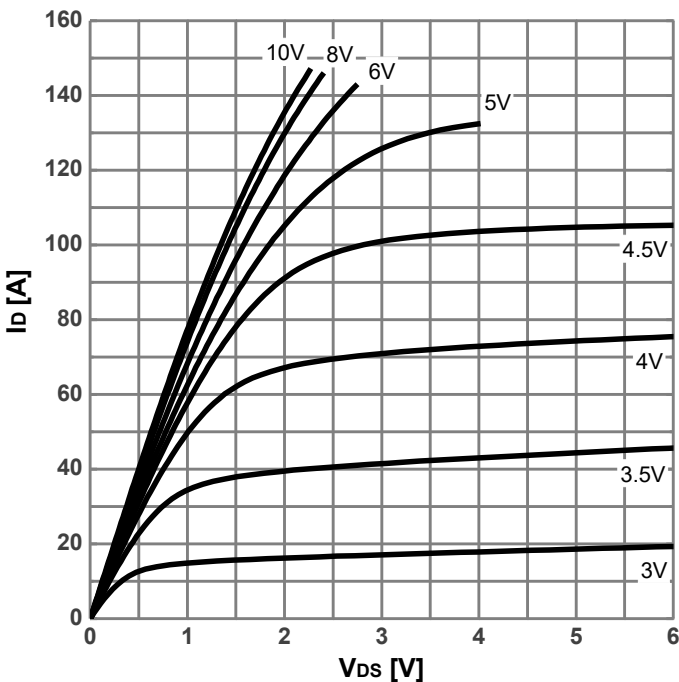
$$V_{GS} = f(Q_{\text{gate}}); I_D = 14.5\text{A pulsed}; V_{DS} = 30\text{V}$$

Diagram 5: Typ. output characteristics



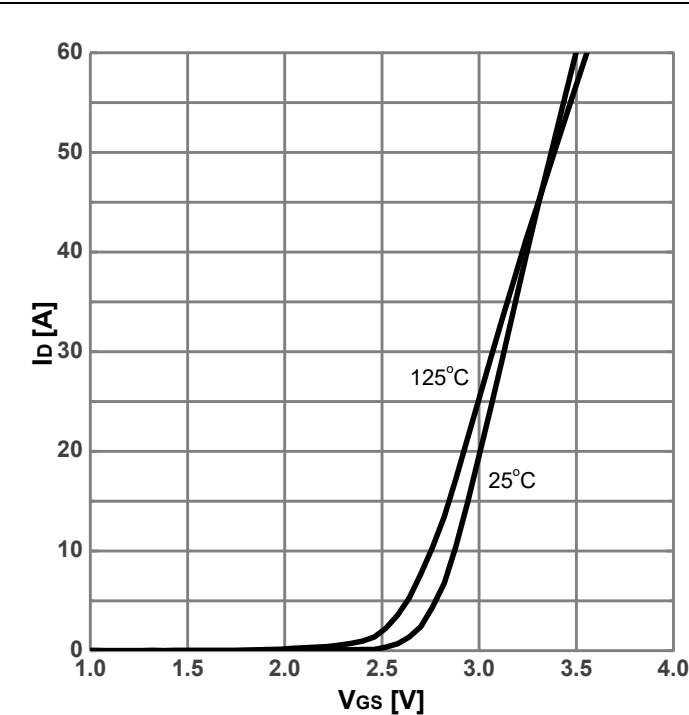
$I_D=f(V_{DS})$; $T_J=25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



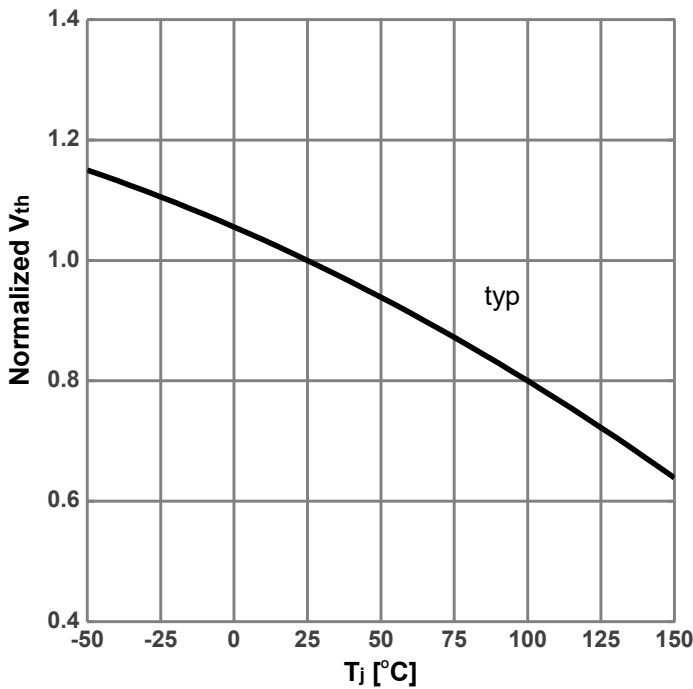
$I_D=f(V_{DS})$; $T_J=125^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



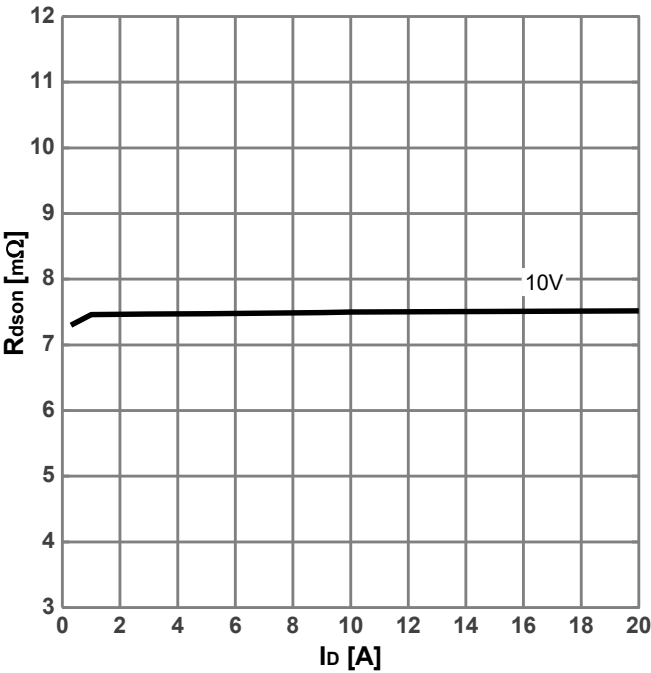
$I_D=f(V_{GS})$; $V_{DS}=15\text{V}$; parameter: T_J

Diagram 8: Gate threshold voltage vs. Junction temperature



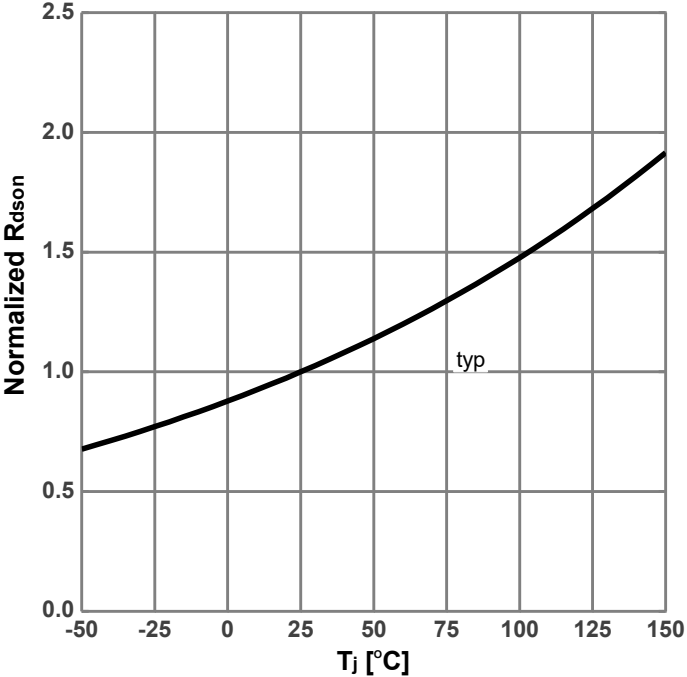
$V_{th}=f(T_J)$; $I_D=250\mu\text{A}$

Diagram 9: On-state resistance vs. Drain current



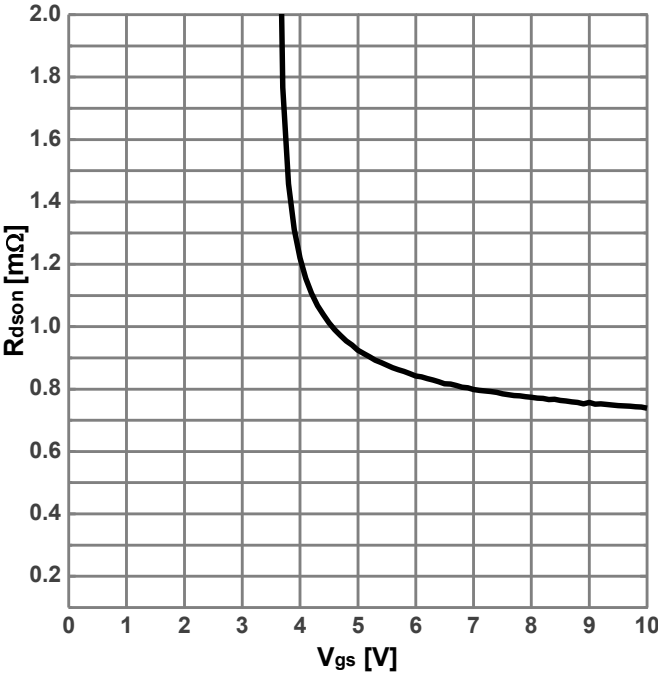
$R_{DS(on)}=f(I_D)$; $T_J=25^\circ C$; parameter: V_{GS}

Diagram 10: On-state resistance vs. Junction temperature



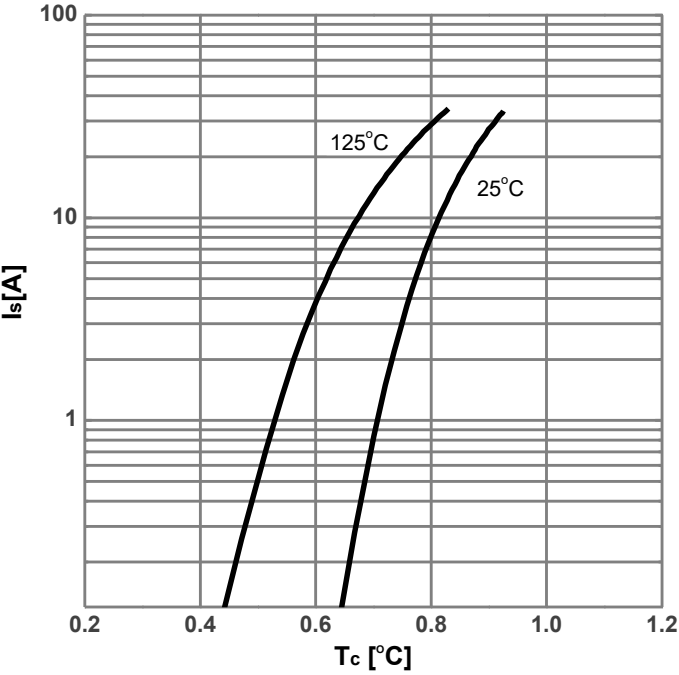
$R_{DS(on)}=f(T_J)$; $I_D=20A$; $V_{GS}=10V$

Diagram 11: On-state resistance vs. Vgs characteristics

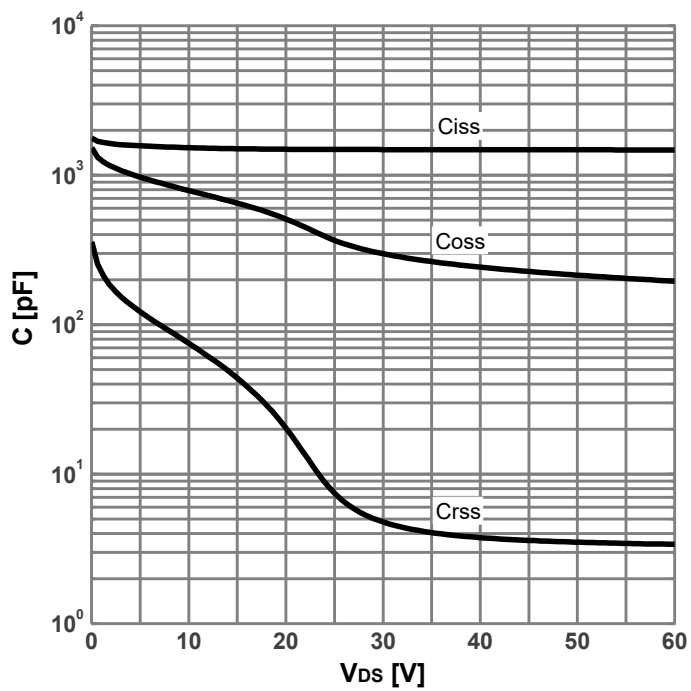


$R_{DS(on)}=f(V_{GS})$; $T_J=25^\circ C$; $I_D=20A$

Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$; parameter: T_J

Diagram 13: Typ. capacitances $C=f(V_{DS}); V_{GS}=0V; f=1MHz$

6. Test Circuits

Table 7. Diode Characteristics

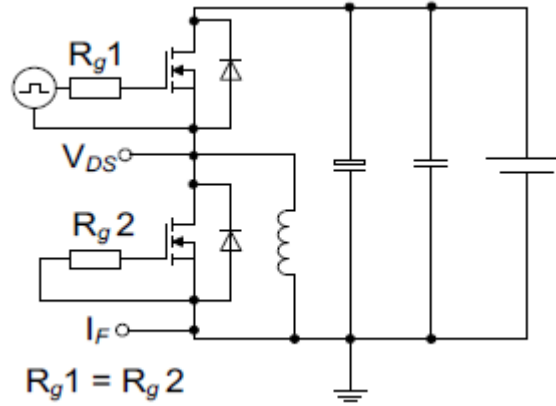
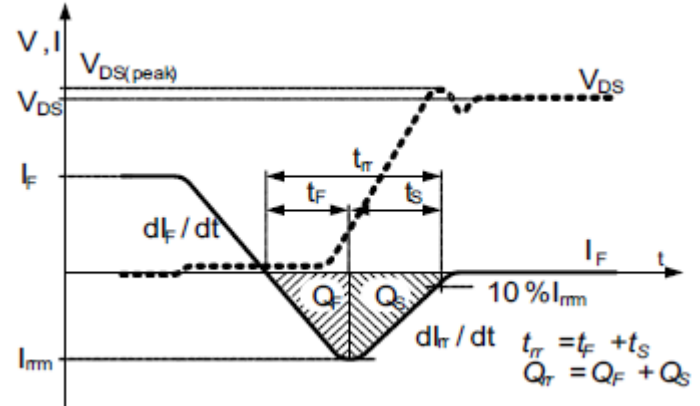
Test circuit for diode characteristics	Diode recovery waveform
	

Table 8. Switching Times

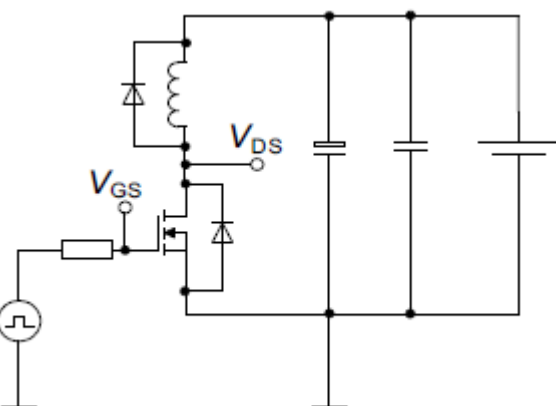
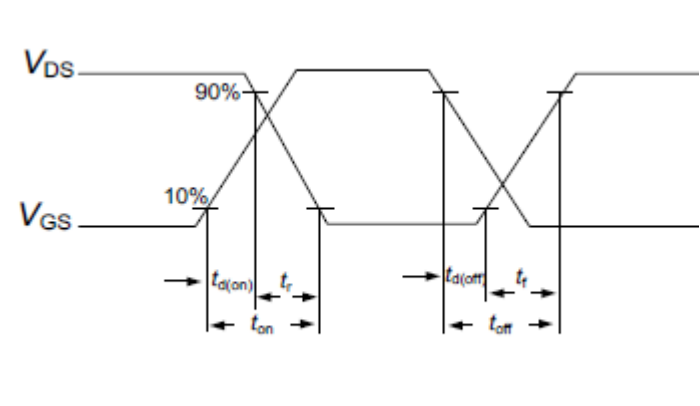
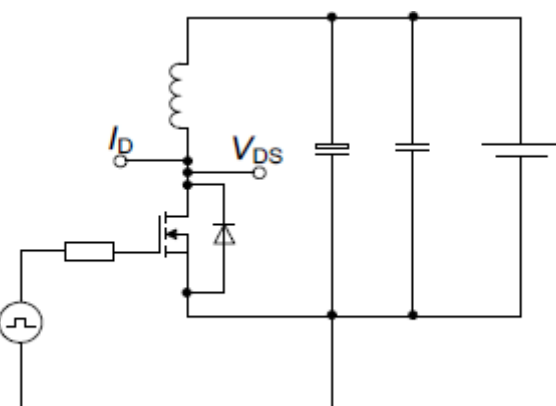
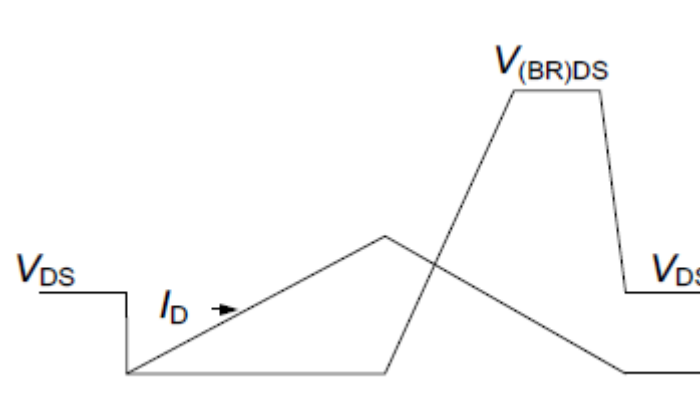
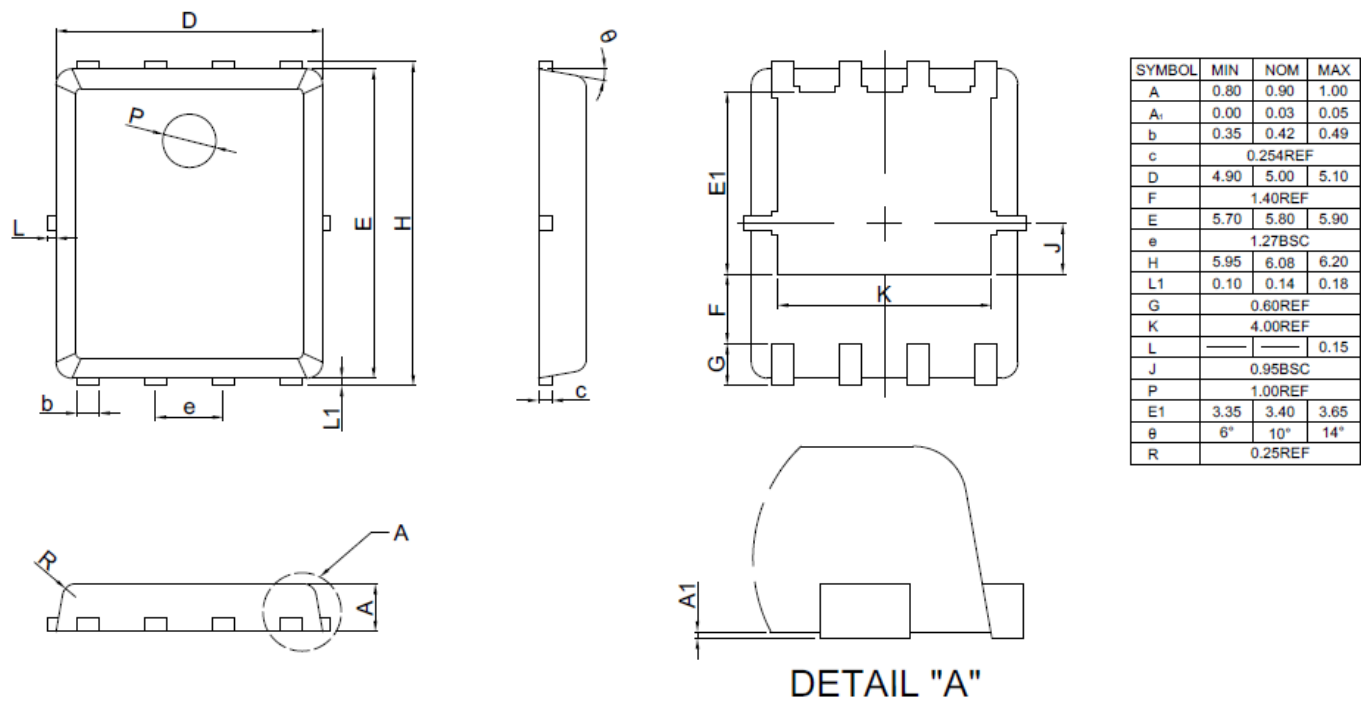
Switching times test circuit for inductive load	Switching times waveform
	

Table 9. Unclamped Inductive Load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7. Package Outlines

Figure 1 Outline DFN5*6 Dimensions in mm



8. Appendix

CoolSemi Webpage: www.coolsemi.com.